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Improved electronic properties of p- epitaxial layers grown on HPHT (100) substrates after a surface pretreatment

Cyrille Barbay¹, Christine Mer-Calfati¹, Nicolas Tranchant¹, Samuel Saada¹, Jean-Charles Arnault¹, Ingrid Stenger², Verena Zuerbig³, N. Lang³, Lutz Kirste³, Oluwasayo Loto⁴, David Eon⁴

¹CEA, LIST, Diamond Sensors Laboratory, F-91191 Gif-sur-Yvette, France

²Groupe d'Etude de la Matière Condensée, Université de Versailles St Quentin, CNRS, Université Paris-Saclay, 45 avenue des Etats-Unis, 78035 Versailles cedex, France

³Fraunhofer Institute for Applied Solid State Physics IAF, 79108 Freiburg, Germany

⁴Institut Néel, Université Grenoble Alpes, 25 Avenue des Martyrs, BP 166, 38042 Grenoble, France

cyrille.barbay@cea.fr

Single-crystal diamond synthesis of high crystalline quality remains a challenge for power electronic devices¹. Usually, HPHT diamond substrates will undergo a mechanical polishing step which induces plastic deformation and dislocations in the subsurface at few microns depth². During Chemical Vapour Deposition (CVD) growth, these dislocations might thread into the epilayers³ and emerge as pyramidal hillocks⁴ affecting the devices electronic performance⁵. Consequently, removing this defective layer and reaching very smooth substrate surface before growth⁶ is primordial to better control the crystalline quality of diamond epitaxial layers.

In this work, we investigated the effect of Ar/O₂ etching on HPHT (100) Ib Sumitomo substrates by optimizing the RF-power, the pressure and the O₂ content in regard to the etching rate and RMS roughness. This surface pretreatment provides fast etching rates up to 9 μm/h and results in smooth surfaces according to AFM measurements (RMS roughness from 3.5 to 2 nm on 40x40 μm² images).

Ar/O₂ etching with optimal conditions was used to lead a comparative study on two half-etched HPHT (100) substrates of different suppliers (Sumitomo Ib and New Diamond Technology IIa). Pretreatment efficiency was tested on both of them by evaluating the enhancement of crystalline quality using Raman Spectroscopy and High Resolution X-ray Diffraction.

The crystalline quality of low boron doped (10¹⁶ cm⁻³) epilayers (2 μm thick) grown simultaneously on the two etched substrates was studied by Raman and Cathodoluminescence and compared with non-treated substrates. SEM voltage contrast is used to highlight the threading dislocations on non-pretreated areas and their removal after etching (Figure 1). Electronic properties were also investigated by Hall measurements and show a clear improvement in term of carrier mobility and resistivity (from 3 to 1.7 Ω.m) on pre-etched area of Ib Sumitomo substrates.

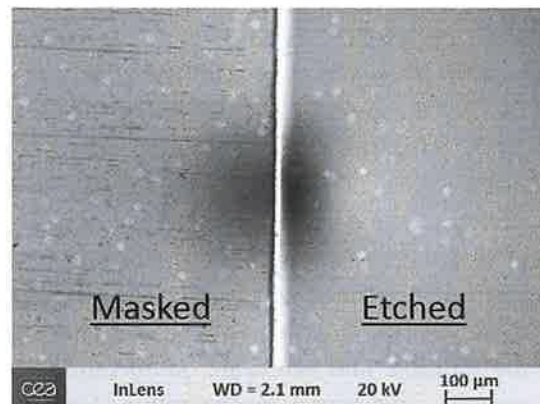


Figure 1: SEM image of half-etched Sumitomo substrate at 20 kV

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